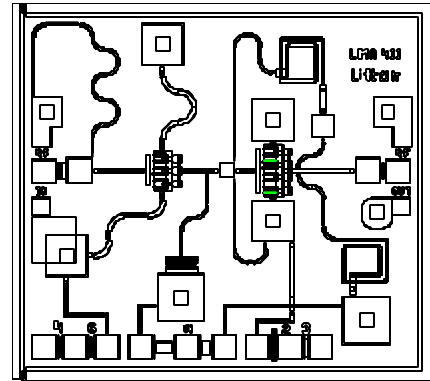


- FEATURES**

- ◆ 8.5 GHz to 14 GHz Frequency Band
- ◆ 2 dB Noise Figure
- ◆ 18 dB Gain
- ◆ 19 dBm Output Power at Saturation
- ◆ +6 V Single Bias Supply



- DESCRIPTION AND APPLICATIONS**

The Filtronic Solid State LMA411 is a high dynamic range low noise PHEMT amplifier that operates from 8.5 to 14GHz. Reactively matched 2-stage amplifier provides 18dB nominal gain with 2dB typical noise figure and 1-dB gain compression power output of +17dBm that can be used as a pre-driver amplifier for phased array radar as well as commercial communications applications. Ground is provided to the circuitry through vias to the backside metallization.

- ELECTRICAL SPECIFICATIONS @  $T_{\text{Ambient}} = 25^{\circ}\text{C}$**

( $V_{\text{DD}} = +6.0\text{V}$ ,  $Z_{\text{IN}} = Z_{\text{OUT}} = 50\Omega$ )

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Frequency Band	F		8.5		14	GHz
Small Signal Gain	$S_{21}$	$R_S = 10/50\Omega$ , $I_{\text{DS}} = 50\% I_{\text{DSS}}$	17	18		dB
Saturated Drain Current	$I_{\text{DSS}}$	$R_S = 0/0\Omega$	105	225	315	mA
Small Signal Gain Flatness	$\Delta S_{21}$			$\pm 0.8$	$\pm 1.2$	dB
Noise Figure	NF			2	3.5	dB
Power at 1-dB Compression	P-1dB			17		dBm
Output Power at Saturation	$P_{\text{SAT}}$		19			dBm
Input Return Loss	$S_{11}$			-10		dB
Output Return Loss	$S_{22}$			-14		dB
Reverse Isolation	$S_{12}$			-34		dB

- ABSOLUTE MAXIMUM RATINGS

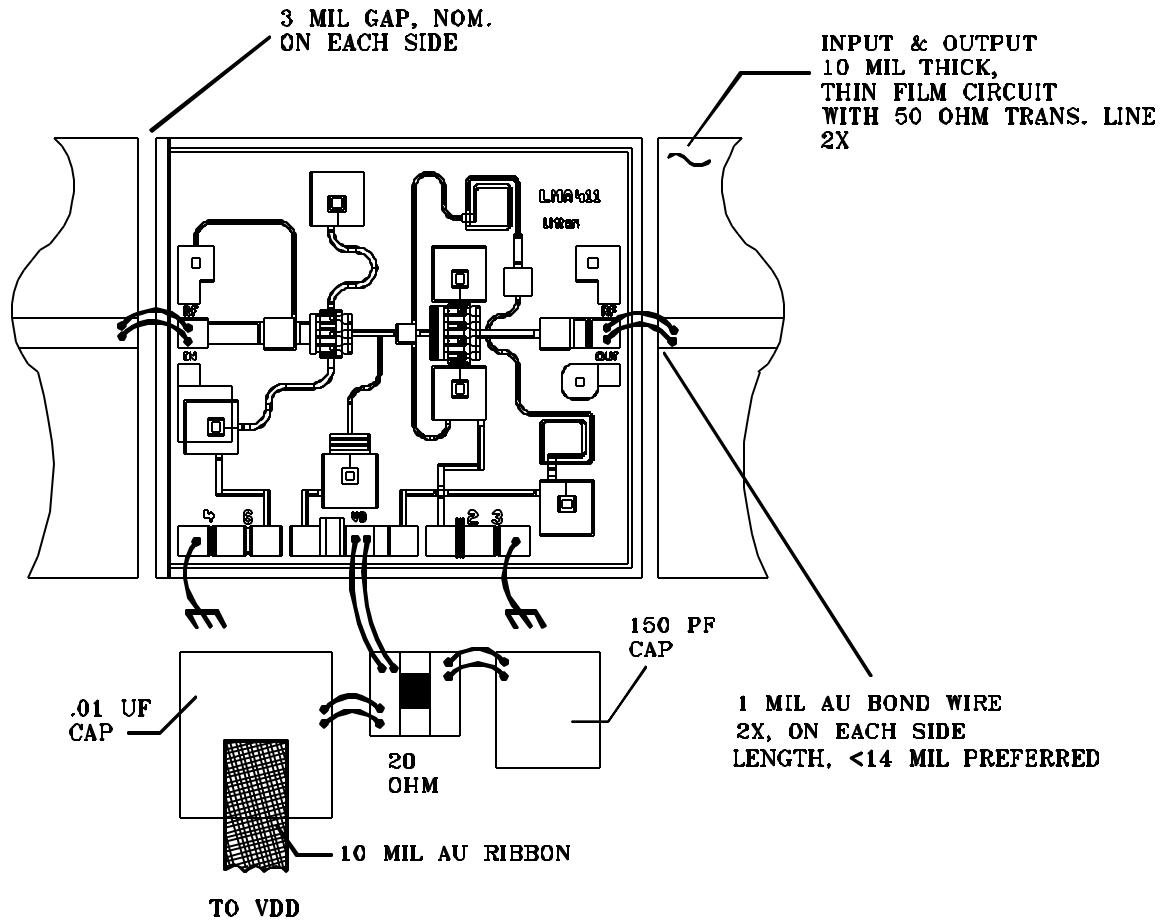
Parameter	Symbol	Test Conditions	Min	Max	Units
Drain Voltage	$V_D$	$T_{\text{Ambient}} = 22 \pm 3 \text{ }^\circ\text{C}$		7	V
Operating Current	$I_{OP}$	$T_{\text{Ambient}} = 22 \pm 3 \text{ }^\circ\text{C}$		315	mA
RF Input Power	$P_{IN}$	$T_{\text{Ambient}} = 22 \pm 3 \text{ }^\circ\text{C}$		15	dBm
Total Power Dissipation	$P_{TOT}$	$T_{\text{Ambient}} = 22 \pm 3 \text{ }^\circ\text{C}$		2	W
Channel Operating Temperature	$T_{CH}$	$T_{\text{Ambient}} = 22 \pm 3 \text{ }^\circ\text{C}$		150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	—	-65	165	$^\circ\text{C}$
Maximum Assembly Temperature (1 min. max.)	$T_{MAX}$	—		300	$^\circ\text{C}$

Notes:

- Operating conditions that exceed the Absolute Maximum Ratings could result in permanent damage to the device.
- Recommended Continuous Operating Limits should be observed for reliable device operation.
- Power Dissipation defined as:  $P_{TOT} \equiv (P_{DC} + P_{IN}) - P_{OUT}$ , where  
 $P_{DC}$ : DC Bias Power  
 $P_{IN}$ : RF Input Power  
 $P_{OUT}$ : RF Output Power
- This GaAs MMIC is susceptible to damage from Electrostatic Discharge. Proper precautions should be used when handling these devices.

• ASSEMBLY DRAWING

**50% of Idss BIAS**

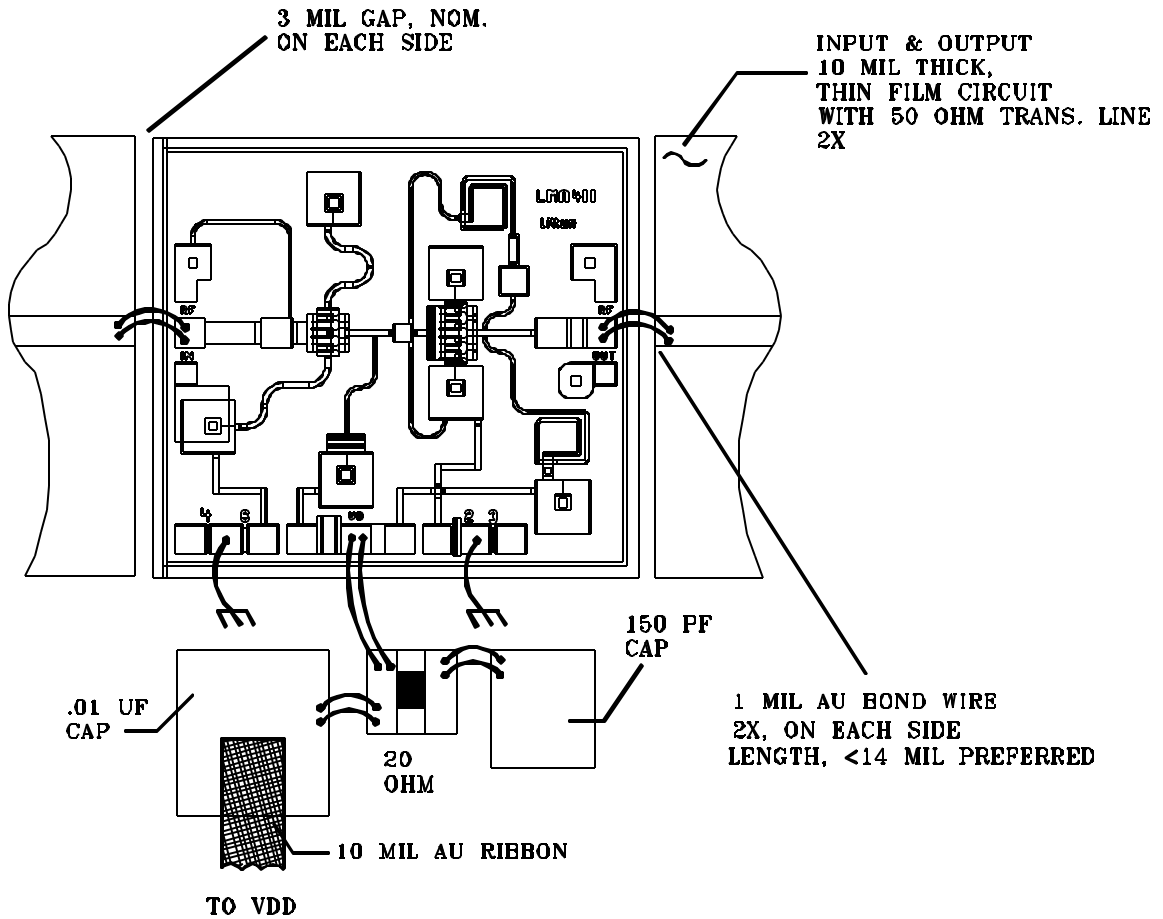


Notes:

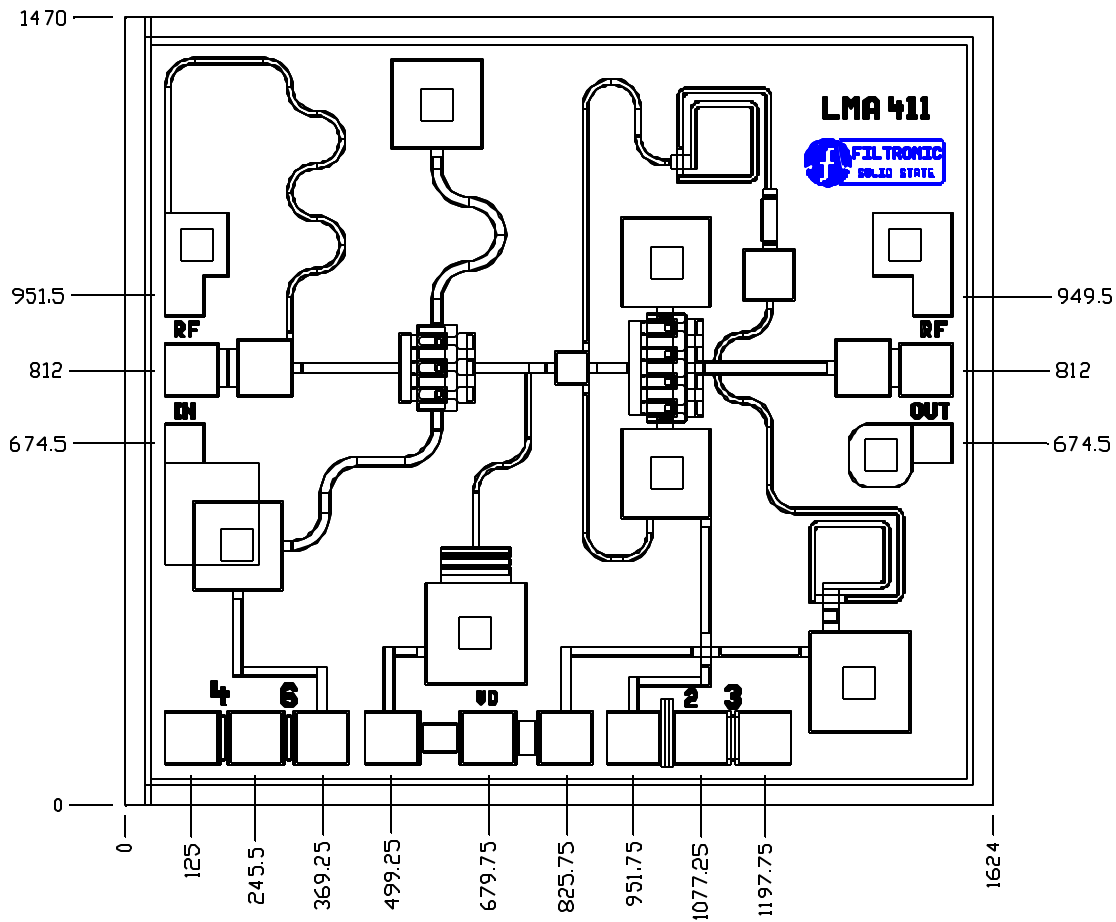
- Recommended lead bond technique is thermocompression wedge bonding with 0.001" (25µm) diameter wire. The bond tool force shall be 35-38 gram. Bonding stage temperature shall be 230-240°C, heated tool (150-160°C) is recommended. Ultrasonic bonding is not recommended.
- The recommended die attach is a eutectic 80/20 Gold/Tin solder, using a stage temperature of 285-290°C. Maximum time at temperature is 1 minute. Use of forming gas (90% N<sub>2</sub>, 10% H<sub>2</sub>) for best results.
- Bond on bond or stitch bond acceptable.
- Conductor over conductor acceptable. Conductors must not short.

- ASSEMBLY DRAWING

75% of Idss BIAS



- MECHANICAL OUTLINE



Notes:

- All units are in microns ( $\mu\text{m}$ ).
- All bond pads are  $100 \times 100 \mu\text{m}^2$ .
- 
- Unless otherwise specified.

- HANDLING PRECAUTIONS

To avoid damage to the devices care should be exercised during handling. Proper Electrostatic Discharge (ESD) precautions should be observed at all stages of storage, handling, assembly, and testing. These devices should be treated as Class 1A (0-500 V). Further information on ESD control measures can be found in MIL-STD-1686 and MIL-HDBK-263.

All information and specifications are subject to change without notice.